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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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2SD1135

Silicon NPN Triple Diffused

RENESAS

ADE-208-906 (Z)

1st. Edition

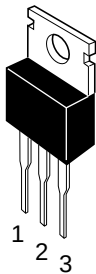
September 2000

Application

Low frequency power amplifier complementary pair with 2SB859

Outline

TO-220AB



- 1. Base
- 2. Collector (Flange)
- 3. Emitter

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	100	V
Collector to emitter voltage	V_{CEO}	80	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	4	A
Collector peak current	$I_{C(peak)}$	8	A
Collector power dissipation	P_C^{*1}	40	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-45 to +150	°C

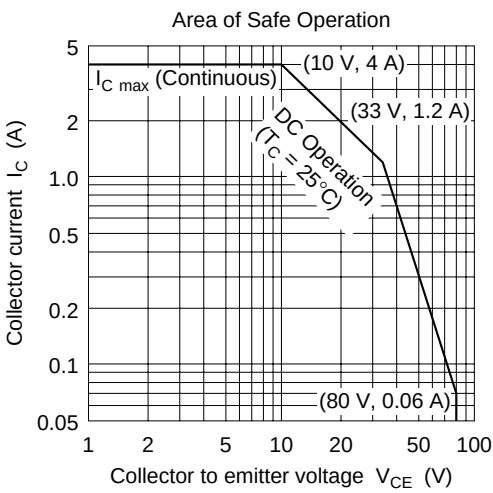
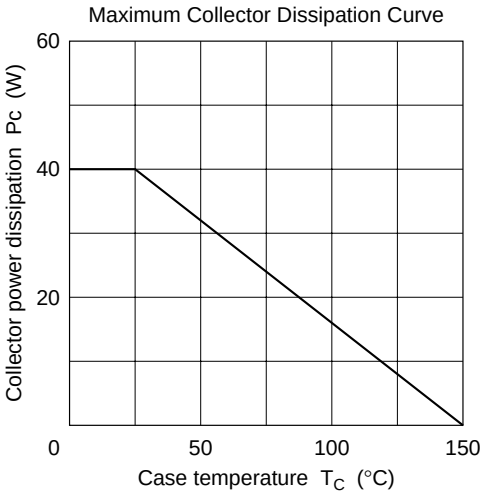
Note: 1. Value at $T_C = 25^\circ\text{C}$.

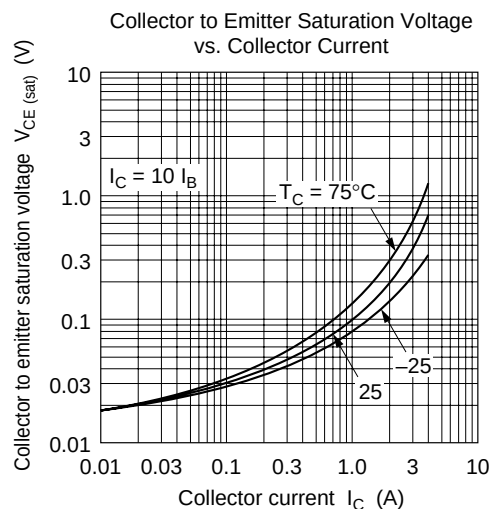
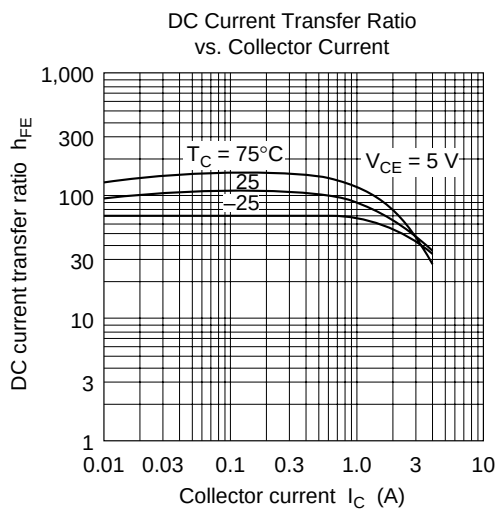
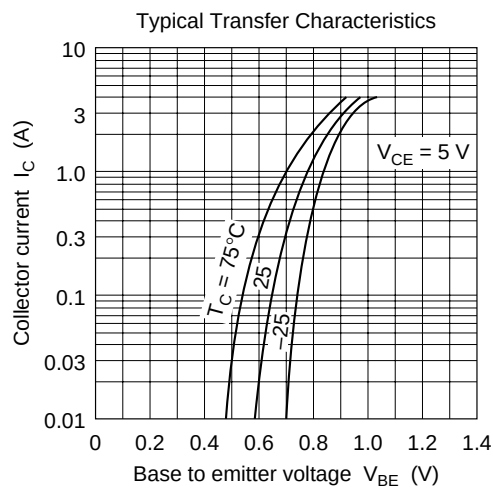
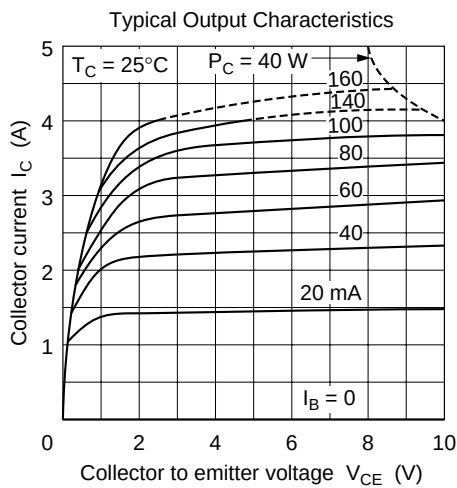
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	80	—	—	V	$I_C = 50\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10\text{ }\mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.1	mA	$V_{CB} = 80\text{ V}$, $I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	200		$V_{CE} = 5\text{ V}$, $I_C = 1\text{ A}^{*2}$
	h_{FE2}	35	—	—		$V_{CE} = 5\text{ V}$, $I_C = 0.1\text{ A}^{*2}$
Base to emitter voltage	V_{BE}	—	—	1.5	V	$V_{CE} = 5\text{ V}$, $I_C = 1\text{ A}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	2	V	$I_C = 2\text{ A}$, $I_B = 0.2\text{ A}^{*2}$
Gain bandwidth product	f_T	—	10	—	MHz	$V_{CE} = 5\text{ V}$, $I_C = 0.5\text{ A}^{*2}$
Collector output capacitance	C_{ob}	—	40	—	pF	$V_{CB} = 20\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$

Notes: 1. The 2SD1135 is grouped by h_{FE1} as follows.
2. Pulse test.

B	C
60 to 120	100 to 200





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